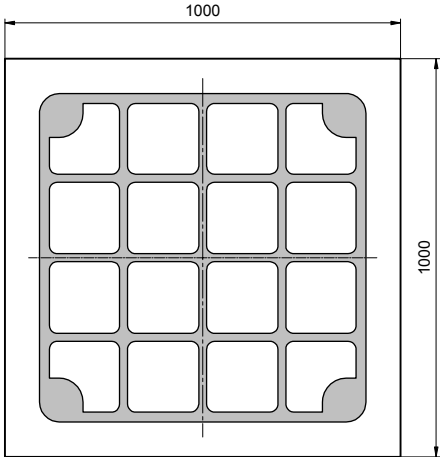


Radiation	Type	Technology	Electrodes
Infrared	DDH	AlGaAs/AlGaAs	N (cathode) up

	typ. dimensions (μm)	
	<u>typ. thickness</u> 150 (± 25) μm <u>cathode</u> gold alloy, 1.5 μm <u>anode</u> gold alloy, 0.5 μm dotted, 25% covered	

Optical and Electrical Characteristics

$T_{\text{amb}} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.7	1.9	V
Forward voltage ²	$I_F = 300 \text{ mA}$	V_F		2.0		V
Reverse voltage	$I_R = 10 \mu\text{A}$	V_R	5			V
Radiant power ¹	$I_F = 300 \text{ mA}$	Φ_e	9.5	12		mW
Radiant power ²	$I_F = 300 \text{ mA}$	Φ_e		24		mW
Peak wavelength ¹	$I_F = 20 \text{ mA}$	λ_P	730	740	750	nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		35		nm
Switching time	$I_F = 20 \text{ mA}$	t_r, t_f		50		ns

¹Measured on bare chip on TO-18 header

²Measured on epoxy covered chip on TO-18 header in copper heat sink (for information only)

Note: All measurements carried out with *EPIGAP* equipment

Labeling

Type	Lot N°	$\Phi_e(\text{typ})$ [mW]	$V_F(\text{typ})$ [V]	Quantity
ELC-740-21				

Packing: Chips on adhesive film with wire-bond side on top